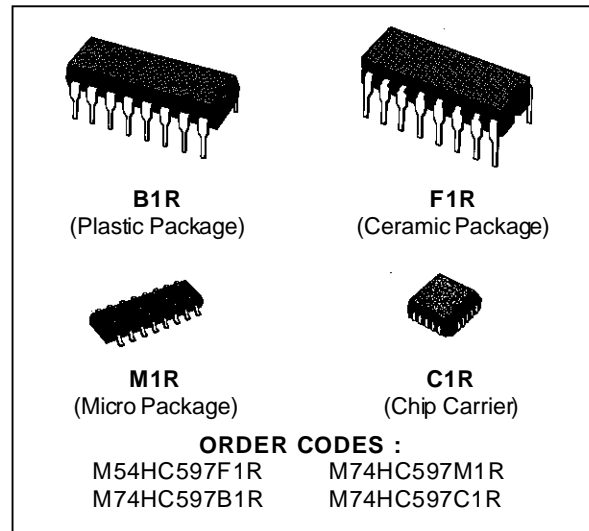


8 BIT LATCH/SHIFT REGISTER

- HIGH SPEED
f_{MAX} = 60 MHz (TYP.) AT V_{CC} = 5 V
- LOW POWER DISSIPATION
I_{CC} = 4 μA (MAX.) AT T_A = 25 °C
- HIGH NOISE IMMUNITY
V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
|I_{OH}| = I_{OL} = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS
t_{PLH} = t_{PHL}
- WIDE OPERATING VOLTAGE RANGE
V_{CC} (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE
WITH 54/74LS597



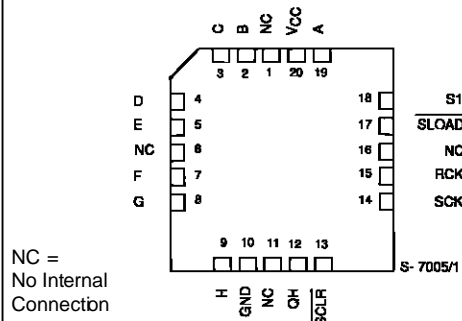
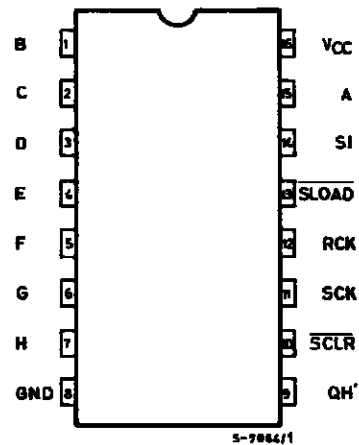
DESCRIPTION

The M54/74HC597 is a high speed CMOS 8-BIT LATCH/SHIFT REGISTER fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption.

This devices comes in a 16-pin package and consist of an 8-bit storage latch feeding a parallel-in, serial-out 8-bit shift register. Both the storage register and shift register have positive-edge triggered clocks. The shift register also has direct load (from storage) and clear inputs.

All inputs are equipped with protection circuits against static discharge and transient voltage excess.

PIN CONNECTIONS (top view)



INPUT AND OUTPUT EQUIVALENT CIRCUIT

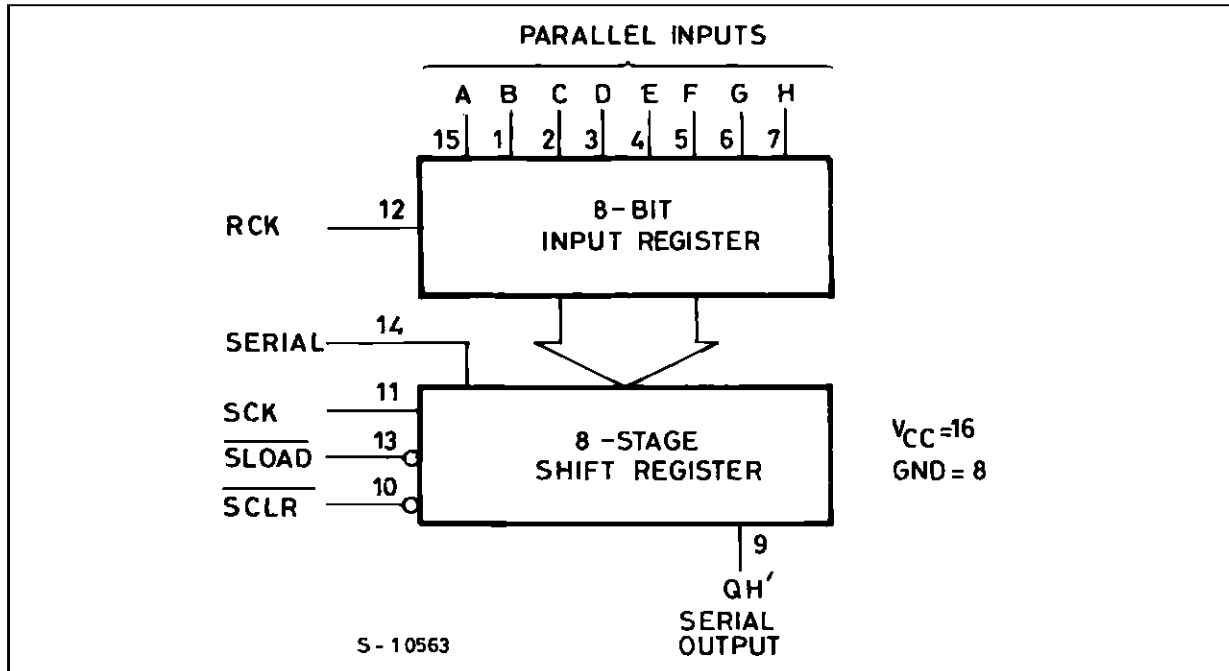


TRUTH TABLE

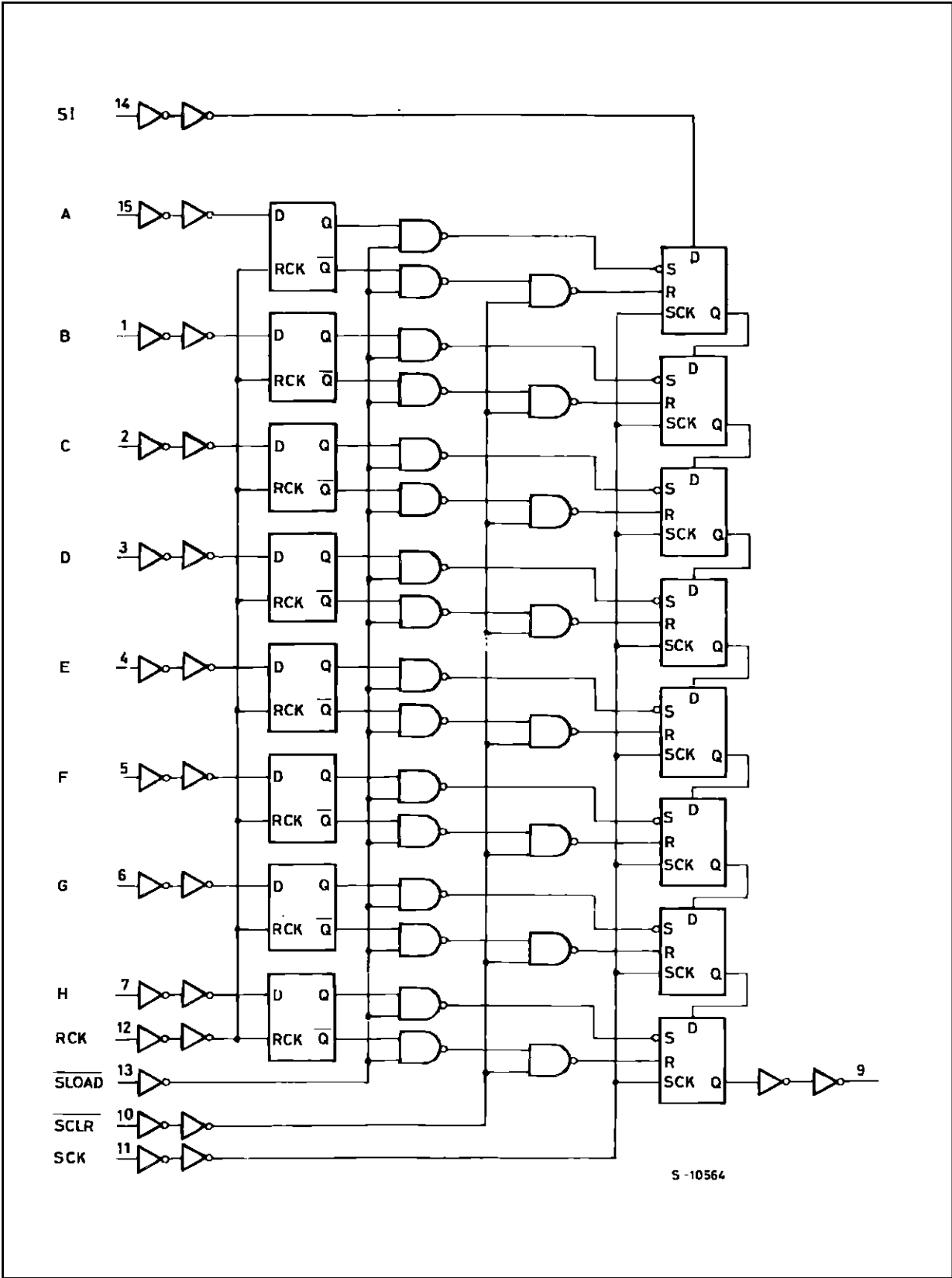
INPUTS					OUTPUT
SI	SCK	SCLR	SLOAD	RCK	
X	X	L	H	X	S.R. IS CLEARED TO "L"
X	X	H	L	X	INPUT REGISTER DATA IS STORED INTO S.R.
L	┌	H	H	X	FIRST STAGE OF S.R. BECOMES "L" OTHER STAGES STORE THE DATA OF PREVIOUS STAGE, RESPECTIVELY
H	┌	H	H	X	FIRST STAGE OF S.R. BECOMES "H" OTHER STAGES STORE THE DATA OF PREVIOUS STAGE, RESPECTIVELY
X	└	H	H	X	STATE OF S.R IS NOT CHANGED
X	X	X	X	┌	INPUT DATA ON A ~ H LINE IS STORED INTO INPUT REGISTER
X	X	X	X	└	STORAGE REGISTER STATE IS NOT CHANGED

X: DON'T CARE

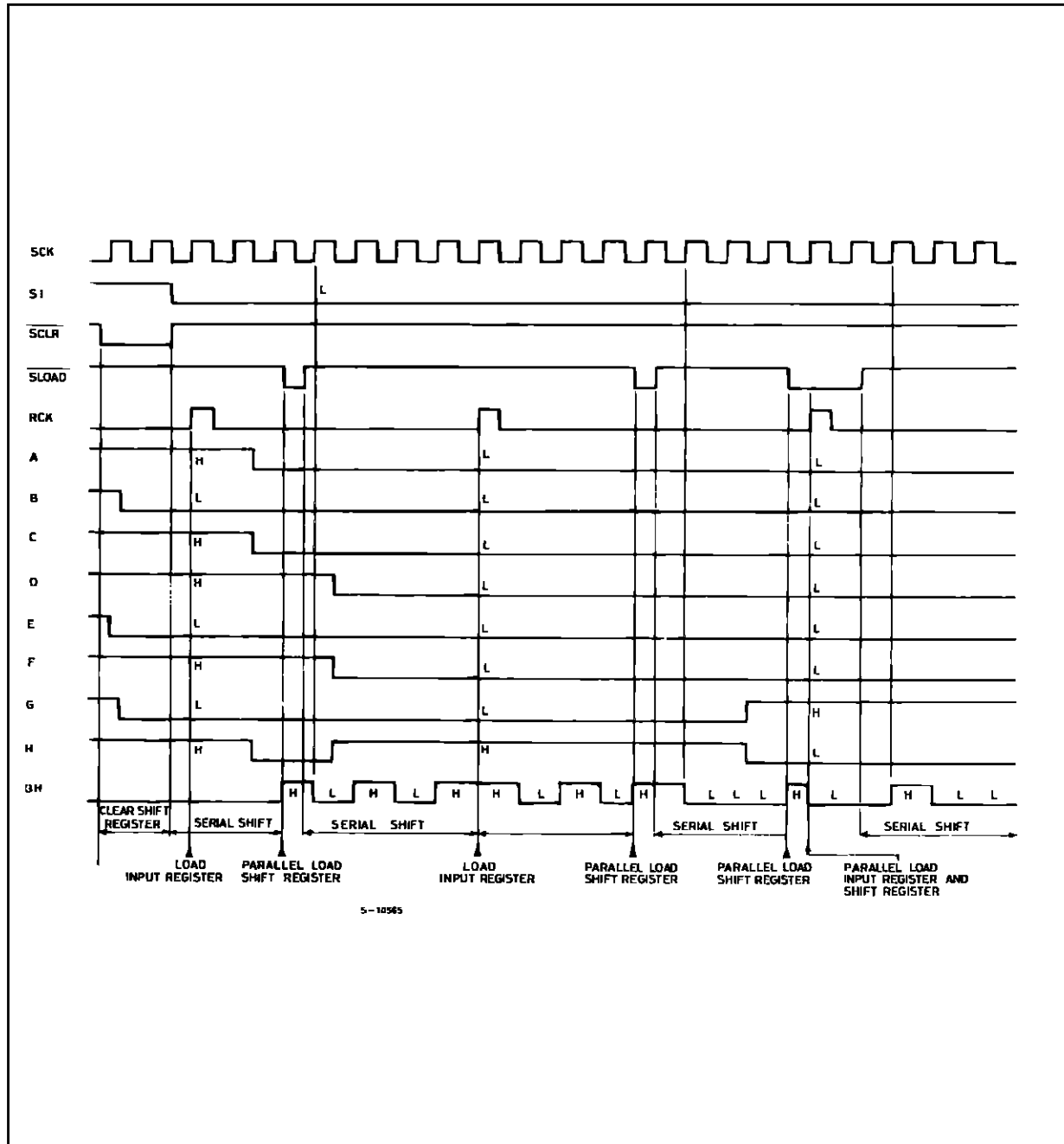
LOGIC DIAGRAM



LOGIC DIAGRAM



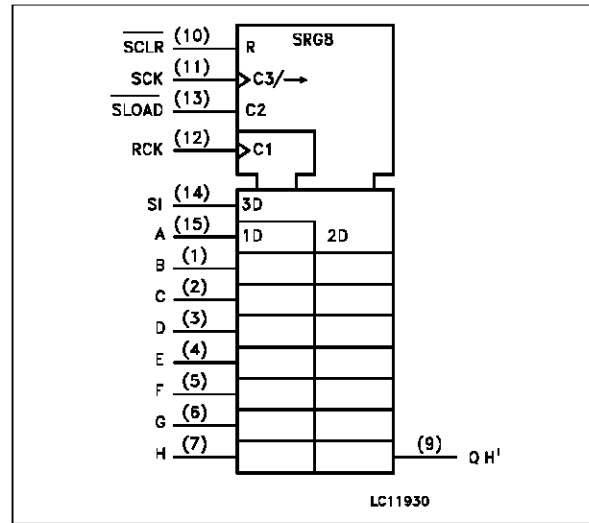
TIMING CHART



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
9	QH'	Serial Data Outputs
10	SCLR	Asynchronous Reset Input (Active LOW)
11	SCK	Shift Clock Input (LOW to HIGH Edge-triggered)
12	RCK	Storage Clock Input (LOW to HIGH Edge-triggered)
13	SLOAD	Parallel Data Input (Active LOW)
10	SI	Serial Data Input
15, 1, 2, 3, 4, 5, 6, 7	A to H	Parallel Data Inputs
8	GND	Ground (0V)
16	V _{CC}	Positive Supply Voltage

IEC LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.
 (*) 500 mW: ≡ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V _{CC}	Supply Voltage	2 to 6	V	
V _I	Input Voltage	0 to V _{CC}	V	
V _O	Output Voltage	0 to V _{CC}	V	
T _{op}	Operating Temperature: M54HC Series M74HC Series	-55 to +125 -40 to +85	°C °C	
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2 V V _{CC} = 4.5 V V _{CC} = 6 V	0 to 1000 0 to 500 0 to 400	ns

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value						Unit		
		V _{CC} (V)		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC			
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.	
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V	
		4.5		3.15			3.15		3.15			
		6.0		4.2			4.2		4.2			
V _{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V	
		4.5				1.35		1.35		1.35		
		6.0				1.8		1.8		1.8		
V _{OH}	High Level Output Voltage	2.0	V _I = V _{IH} or V _{IL}	I _O = -20 μA	1.9	2.0		1.9		1.9	V	
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I _O = -4.0 mA	4.18	4.31		4.13		4.10		
		6.0			I _O = -5.2 mA	5.68	5.8		5.63			5.60
V _{OL}	Low Level Output Voltage	2.0	V _I = V _{IH} or V _{IL}	I _O = 20 μA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I _O = 4.0 mA	0.17	0.26		0.33		0.40		
		6.0			I _O = 5.2 mA	0.18	0.26		0.33		0.40	
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND			±0.1		±1		±1	μA	
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND			4		40		80	μA	

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

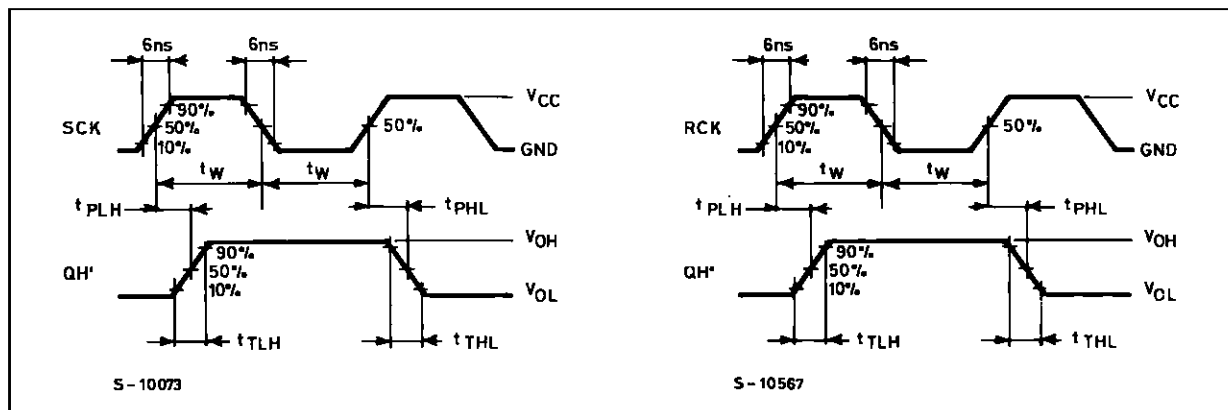
Symbol	Parameter	Test Conditions		Value						Unit	
		V _{CC} (V)		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{TLH} t _{THL}	Output Transition Time	2.0			30	75		95		115	ns
		4.5			8	15		19		23	
		6.0			7	13		16		20	
t _{PLH} t _{PHL}	Propagation Delay Time (SCK - QH')	2.0			78	145		180		220	ns
		4.5			20	29		36		44	
		6.0			16	25		31		37	
t _{PLH} t _{PHL}	Propagation Delay Time (SCLR - QH')	2.0			90	175		220		265	ns
		4.5			24	35		44		53	
		6.0			20	30		37		45	
t _{PLH} t _{PHL}	Propagation Delay Time (SLOAD - QH')	2.0			80	175		220		265	ns
		4.5			22	35		44		53	
		6.0			18	30		37		45	
t _{PLH} t _{PHL}	Propagation Delay Time (RCK - QH')	2.0	SLOAD = "L"		112	210		265		315	ns
		4.5			30	42		53		63	
		6.0			24	36		45		54	

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

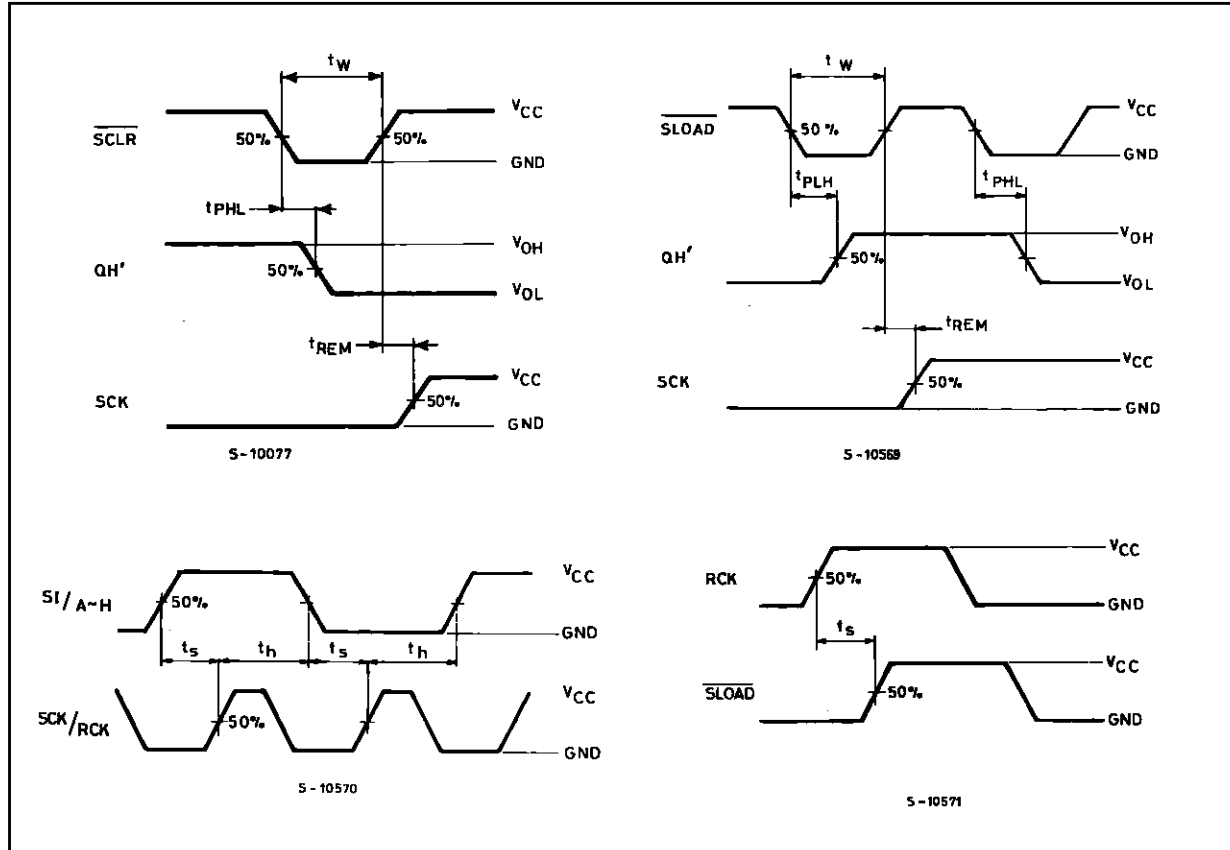
Symbol	Parameter	Test Conditions		Value						Unit	
		V _{CC} (V)		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
f _{MAX}	Maximum Clock Frequency	2.0		6.0	12		4.8		4.0		ns
		4.5		30	48		24		20		
		6.0		35	50		28		24		
t _{W(H)} t _{W(L)}	Propagation Delay Time (SCK, RCK)	2.0			20	75		95		110	ns
		4.5			7	15		19		22	
		6.0			4	13		16		19	
t _{W(L)}	Propagation Delay Time (SCLR, SLOAD)	2.0			25	75		95		110	ns
		4.5			7	15		19		22	
		6.0			5	13		16		19	
t _s	Minimum Set-up Time (RCK - SLOAD)	2.0			48	100		125		150	ns
		4.5			12	20		25		30	
		6.0			10	17		21		26	
t _s	Minimum Set-up Time (SI, SCK)	2.0			20	75		95		110	ns
		4.5			5	15		19		22	
		6.0			4	13		16		19	
t _s	Minimum Set-up Time (PI - RCK)	2.0			20	75		95		110	ns
		4.5			5	15		19		22	
		6.0			4	13		16		19	
t _r	Minimum Hold Time	2.0				0		0		0	ns
		4.5				0		0		0	
		6.0				0		0		0	
t _{REM}	Propagation Delay Time (SCLR, SLOAD)	2.0			12	75		95		115	ns
		4.5			4	15		19		23	
		6.0			3	13		16		20	
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance				60						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(OPR)} = C_{PD} • V_{CC} • f_{IN} + I_{CC}

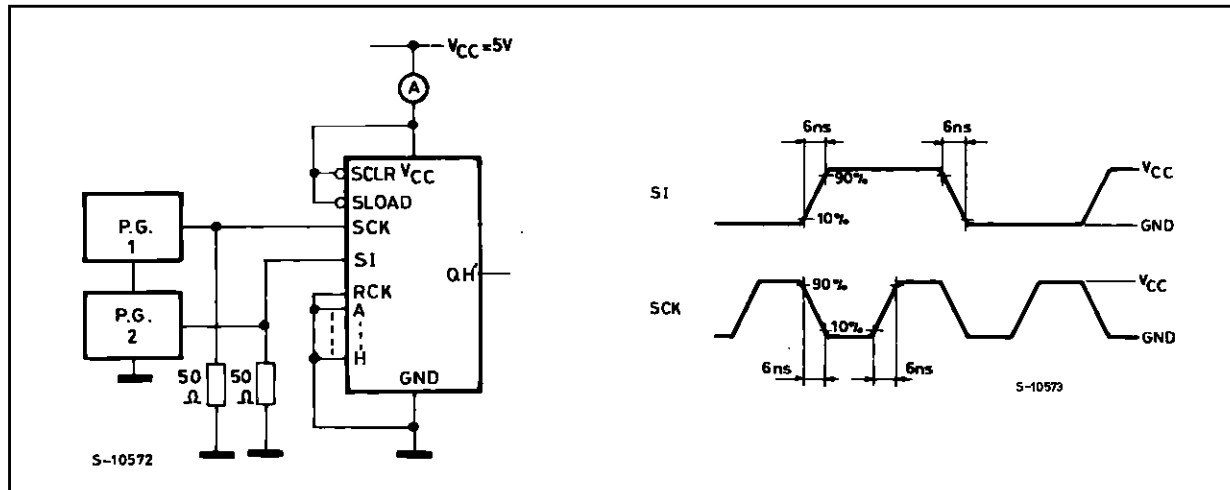
SWITCHING CHARACTERISTICS TEST WAVEFORM



TEST WAVEFORM (continued)



TEST CIRCUIT I_{CC} (Opr.)



Plastic DIP16 (0.25) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



P001C

Ceramic DIP16/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



SO16 (Narrow) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



P013H

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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